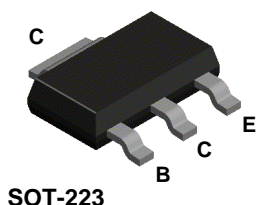


## BCP55



### NPN General Purpose Amplifier

This device is designed for general purpose medium power amplifiers and switching circuits requiring collector currents to 1.0 A. Sourced from Process 38. See BCP54 for characteristics.

#### Absolute Maximum Ratings\*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	60	V
V <sub>CB0</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>c</sub>	Collector Current - Continuous	1.5	A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		BCP55	
P <sub>D</sub>	Total Device Dissipation	1.5	W
	Derate above 25°C	12	mW/°C
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	83.3	°C/W

**NPN General Purpose Amplifier**  
(continued)

**BCP55**

**Electrical Characteristics**

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
<b>OFF CHARACTERISTICS</b>					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = 10 \text{ mA}, I_B = 0$	60		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \text{ } \mu\text{A}, I_E = 0$	60		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ } \mu\text{A}, I_C = 0$	5.0		V
$I_{CBO}$	Collector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_E = 0$ $V_{CB} = 30 \text{ V}, I_E = 0, T_A = 125^\circ\text{C}$		100 10	nA $\mu\text{A}$
$I_{EBO}$	Emitter-Cutoff Current	$V_{EB} = 5.0 \text{ V}, I_C = 0$		10	$\mu\text{A}$
<b>ON CHARACTERISTICS</b>					
$h_{FE}$	DC Current Gain	$I_C = 5.0 \text{ mA}, V_{CE} = 2.0 \text{ V}$ $I_C = 150 \text{ mA}, V_{CE} = 2.0 \text{ V}$ $I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}$	25 40 25	250	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		0.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = 500 \text{ mA}, V_{CE} = 2.0 \text{ V}$		1.0	V

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## PRODUCT STATUS DEFINITIONS

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